

AMENDMENTS

IN THE SPECIFICATION

1) page 16, fourth paragraph, after "for the bond pad.", add:

A1

"The layers of metal that form pattern 12 and pattern 14 are deposited on the surface of a substrate 10."

2) page 16, fourth paragraph, replace "pattern 14" with "pattern 12"

3) page 16, fourth paragraph, replace "pattern 12" with "pattern 14"

4) page 17, line 5, after "Plasma Enhanced", delete " $\text{Si}_3\text{Ni}_4$ " and insert " $\text{Si}_3\text{N}_4$ "

5) page 18 and 19, delete " $\text{SiN}_3$ " and insert " $\text{Si}_3\text{N}_4$ ".

A2

6) page 16, after the fourth paragraph, add: "The top layers of metal for the interconnecting lines 12 and the bond pad 14 can contain aluminum or an aluminum/copper (Al/Cu) alloy. The thickness of the bond pad 14 is equal to the thickness of the interconnect lines 12 and is between 4000 and 8000 Angstroms."

7) page 17, after "above the keyhole 20" of the fourth

A3

paragraph, add: "Shrinkage of up to 40% of the thickness of the polyimide can occur after curing of the layer of photosensitive polyimide."

8) page 16, after "for the bond pad" of the fourth paragraph, add the following new paragraph: "The pattern of interconnect

A4

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lines 12 and the bond pad 14 can also be created on a base layer of SiO<sub>2</sub> that has been created on the surface of a substrate.

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This base layer of SiO<sub>2</sub> is created prior to the creation of the metal layers thereby cushioning the transition of stress between the silicon substrate and the metal layers 12 and 14. In addition, the interconnecting metal and the bond pad metal can be formed on top of any layer of a semiconductor device other than the surface of a semiconductor substrate. Furthermore, the top level interconnecting metal and top-level bond metal can be formed selectively on a bare main surface of a semiconductor substrate in which a desired circuit element is being formed."

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9) page 20, lines ~~12-14~~<sup>11-12</sup>, change "for a time of 20 hours" to "for a time of 2 hours".

10) page 18, remove the third paragraph (lines 14-17).

11) page 18, line 11, after "solvent" add "so that"

#### IN THE CLAIMS

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AS  
Sub 1  
1. (Amended) A method for forming bonding pads of a semiconductor substrate comprising the steps of:

[Providing] providing top [layer] level interconnecting metal for interconnecting lines and top level [metal] bond pad metal for bond pads, said top level metal being formed selectively on an insulating film overlying the main surface of